EXHIBIT D:
MARKED VERSION OF THE CLAIMS
UPON ENTRY OF THE AMENDMENT UNDER 37 C.F.R. § 1.111
IN RESPONSE TO THE OFFICE ACTION MAILED November 6, 2002

U.S. PATENT APPLICATION SERIAL NO. 09/938,435
(ATTORNEY DOCKET NO. 10732-106-999)

1. (Amended) A method of controlling thickness uniformity of [an organosilicate] a film deposited on a [large] substrate, said method comprising the steps of:

providing a [large] substrate in a processing chamber;

controlling a temperature of at least two distinct locations on the [large] substrate [to include] including (i) a perimeter area of a surface of the [large] substrate and (ii) an inner area of the surface that is inside [of] the perimeter area; and

maintaining the temperature of the perimeter area of the surface of the [large] substrate within a range between about 10°C less than the temperature of the inner area [of the surface inside of the perimeter area] to about 20°C higher than the temperature of the inner area [of the surface inside of the perimeter area]; and

depositing the [organosilicate] film, wherein the [organosilicate] film [deposited] has a film thickness uniformity less than or equal to about 10%.

2. (Amended) The method of claim [1] 25, wherein the temperature of the perimeter area of the surface is controlled by a first heater element in a portion of the susceptor [and] that is underlying the perimeter area of the substrate, and the temperature of the inner area [of the surface inside of the perimeter area] is controlled by a second heater element in a portion of the susceptor [and] that is underlying the [area inside of the perimeter] inner area, said controlling comprising maintaining the temperature of the perimeter area of the substrate within a range of about 380°C to about 410°C, while maintaining the inner area [inside of the perimeter area] at about 390°C.

3. (Amended) The method of claim 2, wherein the organosilicate film is produced from a precursor comprising TEOS, and said controlling comprises maintaining the temperature of the perimeter area at about 390°C while maintaining the inner area [areas

inside of the perimeter] at about 390°C.

4. (Amended) The method of claim 2, wherein the organosilicate film is produced from a precursor comprising TEOS, and said controlling comprises maintaining the temperature of the perimeter area [at greater than] between about 390°C [to] and about 400°C while maintaining the inner area [inside of the perimeter] at about 390°C.

5. (Amended) The method of claim 2, wherein the organosilicate film is produced from a precursor comprising TEOS, and said controlling comprises maintaining the temperature of the perimeter area [at greater than] between about 400°C [to] and about 410°C while maintaining the inner area [inside of the perimeter] at about 390°C.

6. (Amended) The method of claim 2, wherein the organosilicate film is produced from a precursor comprising TEOS, and said controlling comprises maintaining the temperature of the perimeter area at about 410°C while maintaining the inner area [inside of the perimeter] at about 390°C.

7. (Amended) The method of claim [1] 25, wherein the temperature of the perimeter area of the surface is controlled by a first heater element in a portion of the susceptor [and] that is underlying the perimeter area of the substrate, and the temperature of the inner area of the surface [inside of the perimeter area] is controlled by a second heater element in a portion of the susceptor [and] that is underlying the inner area [inside of the perimeter area], said controlling comprising maintaining the temperature of the perimeter area within a range of about 350°C to about 460°C, while maintaining the inner area [inside of the perimeter area] within a range of about 340°C to about 450°C.

10. (Amended) The method of claim 1, wherein said depositing [comprises a] is by chemical vapor deposition, physical vapor deposition, plasma enhanced chemical vapor deposition or rapid thermal processing.

12. (Amended) The method of claim 11, wherein said TEOS is inputted into said

processing chamber at about 300 sccm, said He is inputted at about 100 sccm, said oxygen is inputted at about 5000 sccm and said RF energy is inputted at a power density of about .3 to .7 W/cm^2 [and a frequency of about 13.56 MHz].